

METHOD OF FORMING HIGH VOLTAGE METAL OXIDE SEMICONDUCTOR TRANSISTOR

Abstract

A polysilicon layer and a first patterned photoresist layer are formed on a substrate. An ultraviolet curing process is performed to cure the first patterned photoresist layer. Then, a gate structure is formed by using the first patterned photoresist layer as a hard mask. A second patterned photoresist layer is formed on the substrate. The second patterned photoresist layer, the cured remaining first patterned photoresist layer and the gate form two openings alongside the gate structure. Finally, via the openings, two consecutive ion implantation processes are performed to form a double diffuse drain (DDD) structure.